

Variation mapping for analog devices



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Analog Versus Digital (1)

■ Digital

- Gates (level, delay)
- Few interactions
- Binary output
- Testability (DFT, SCAN, BIST)
- Fault propagation (Functional test)

■ Soft defects

- Easy to manage (Dynamic Laser Stimulation: SDL, LADA, ...)

■ Hard defect

- Sometimes tricky (opens, fault propagation, no leakage)

Analog Versus Digital (2)

■ Analog

■ Full set of parameters

- At transistor level
- At device level
- Analogue

■ Interactions between stages (backward coupling)

■ “Poor” testability

■ Soft defects

- Difficult (all the areas are laser sensitive) except some Mixed Mode ASIC (DLS)

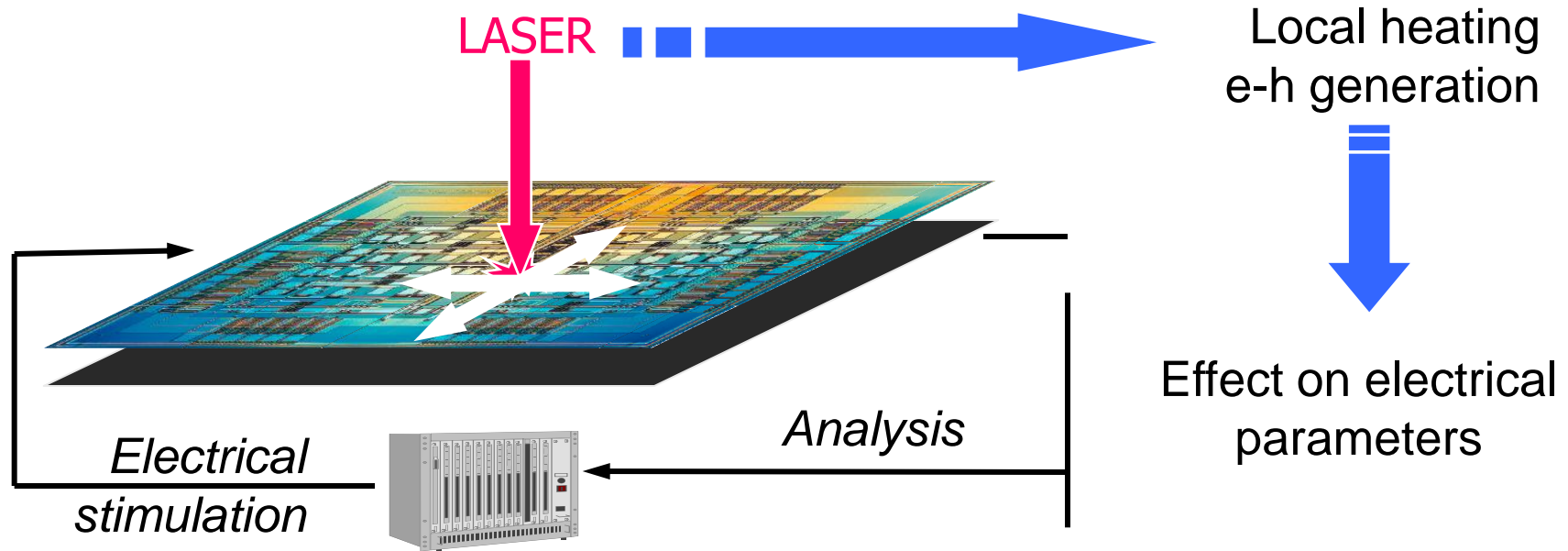
■ Hard defect

- Easier? (no fault propagation)

Needs for analog device

- Measure the analogue parameters at the outputs of the IC
 - Continuous (no longer level / time)
 - Various (voltage, current, bandwidth, distortion, noise ...)
- While few external inputs are available (poor testability)
- Establish the link between external analog measurements and abnormal device behavior
- Verify at elementary structure level (transistor probing)

Laser Stimulation Principle



- Local temperature increase:
 - Resistance change
 - μ , V_T ...
 - Thermal expansion
 - Thermoelectric generation
- Photo electric effect:
 - Current source

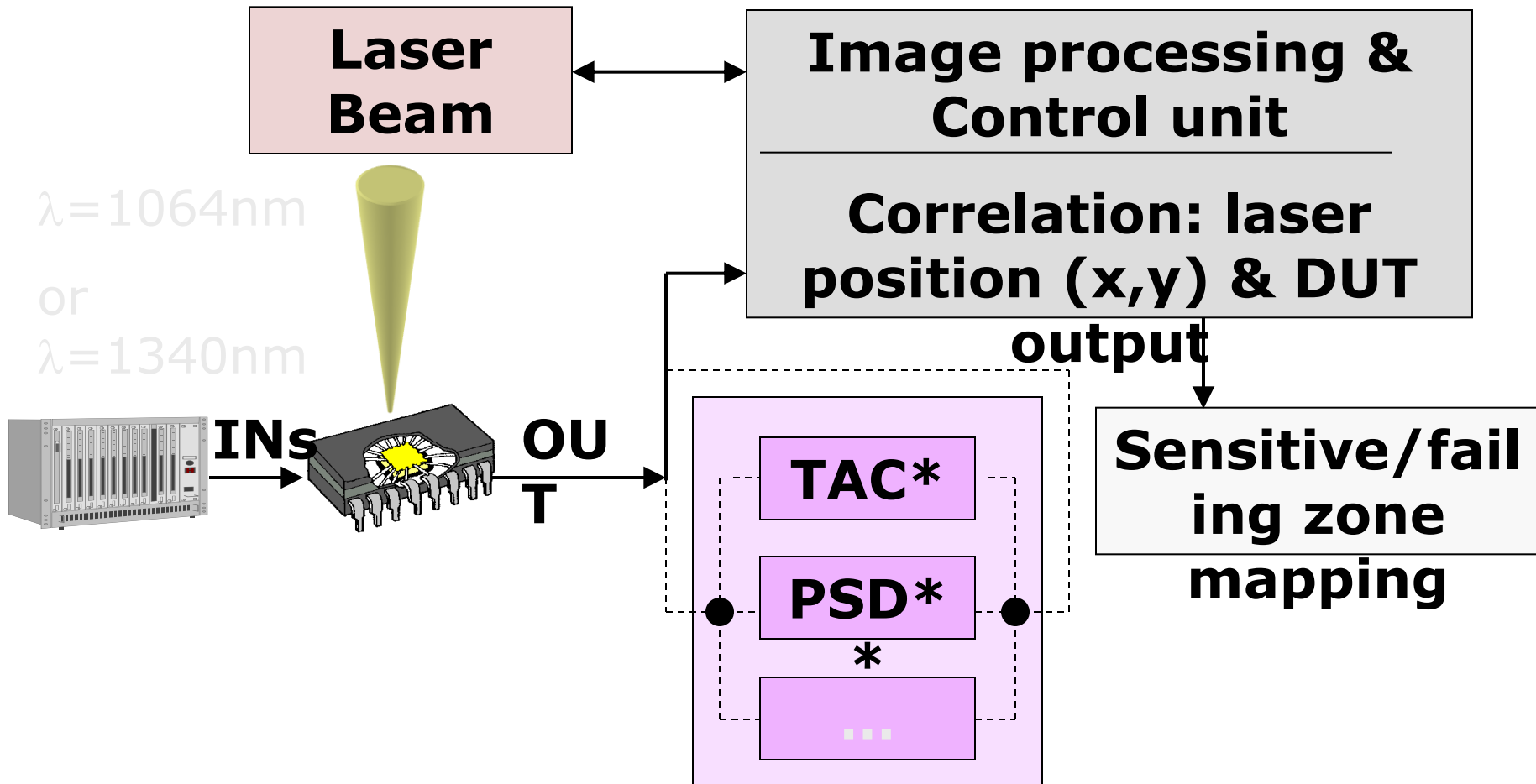
Why laser stimulation?

- Ability to activate internal node
 - All the nodes can be individually activated
 - The effect of the stimuli can be measured outside
- Ability to adjust stimulation
 - Thermal
 - Photoelectric
 - Continuous (analogue modulation)
- Direct measurement of the effects on the IC pins
- Drawback: understand the effect

x Variation Mapping principle

- xVM= x Variation Mapping
 - Laser induces slight electrical changes
 - Analog approach (xVM)
 - Analog measurement of one or more electrical parameters relevant (or not) to the “defective” signature (delay, frequency, voltage,...)
 - Requires dedicated electronics
 - Ex: Analog devices
 - OPA
 - Current mirror/ regulator
 - PWM
 - PLL
 - Comparators
 - Oscillators
 - ...
- Measurable parameters x:
- Output Voltage
 - Current
 - Noise
 - Cut-off frequency
 - Distortions
 - Gain
 - Offset
 - Frequency
 - Phase
 - Delay
 - Duty cycle
 - Pulse width
 - ...

x Variation Mapping setup

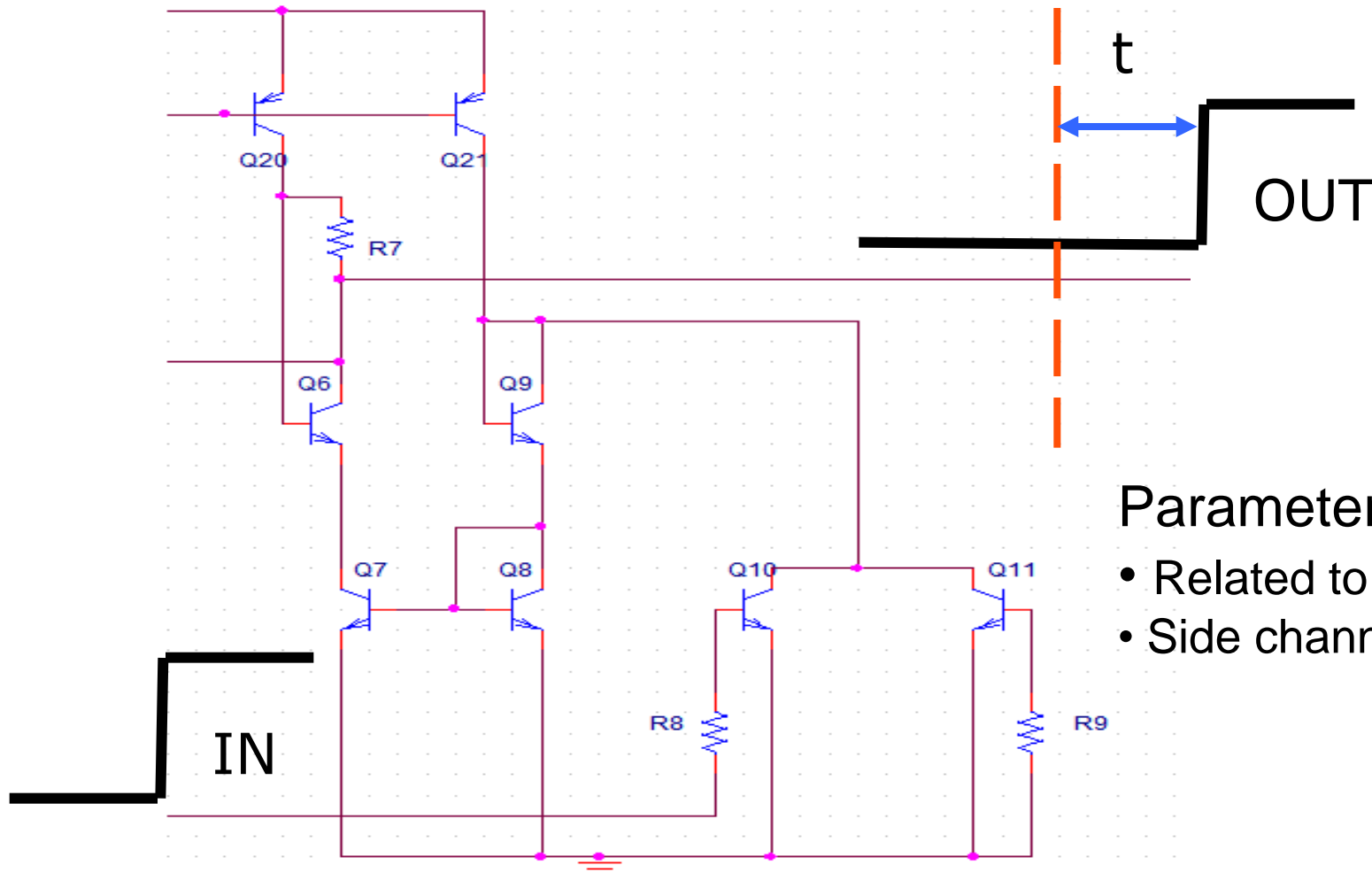


***TAC: Time to Amplitude Converter**

****PSD: Phase Sensitive Detector**

Example: DVM

■ Power Amplifier driver block

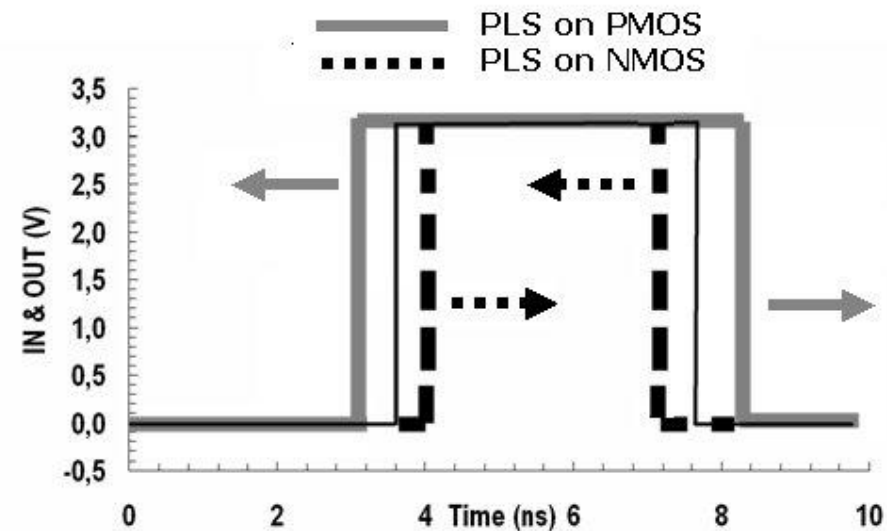
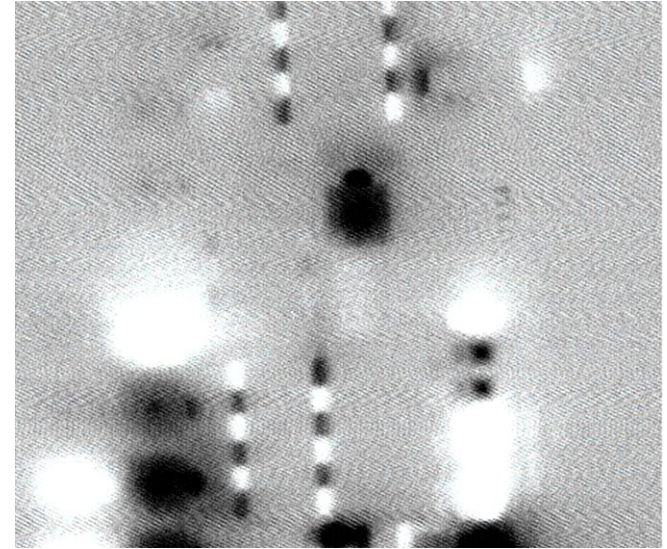


Parameter can be:

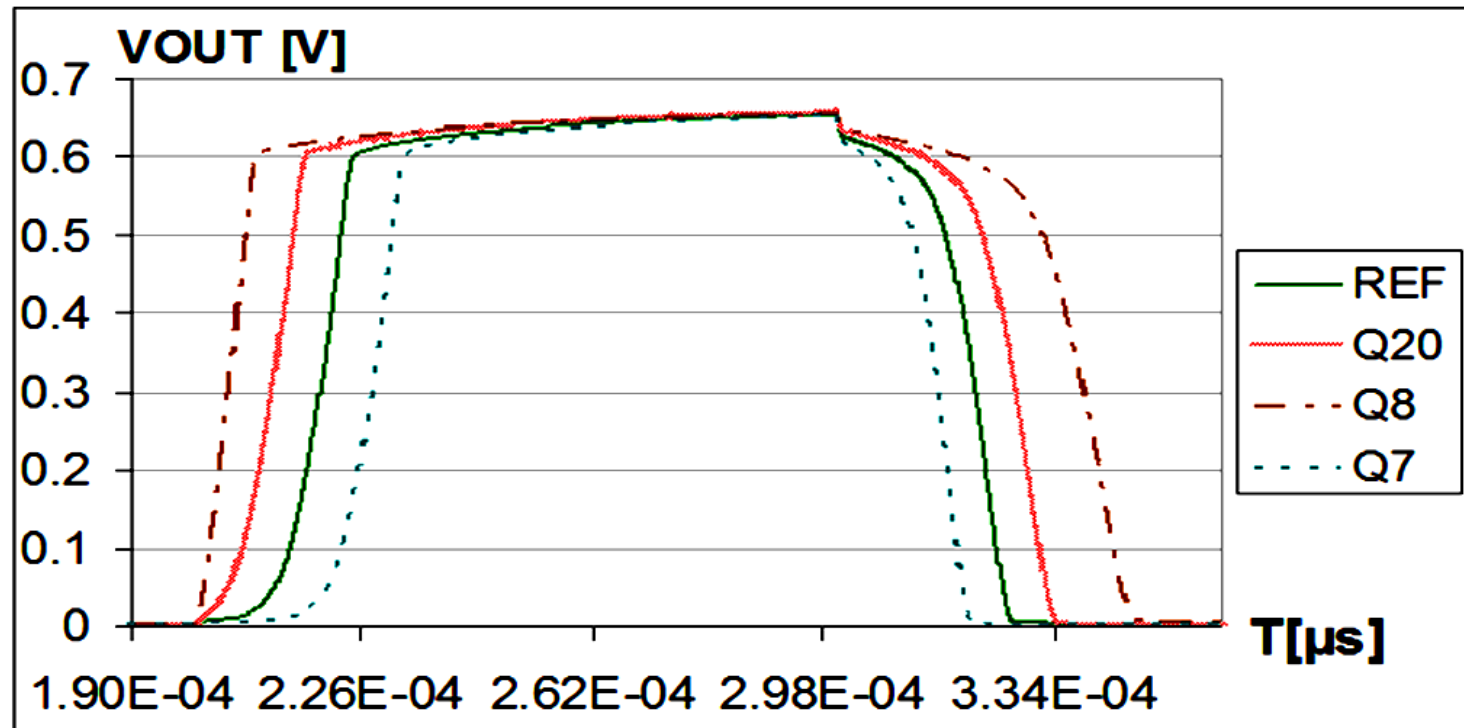
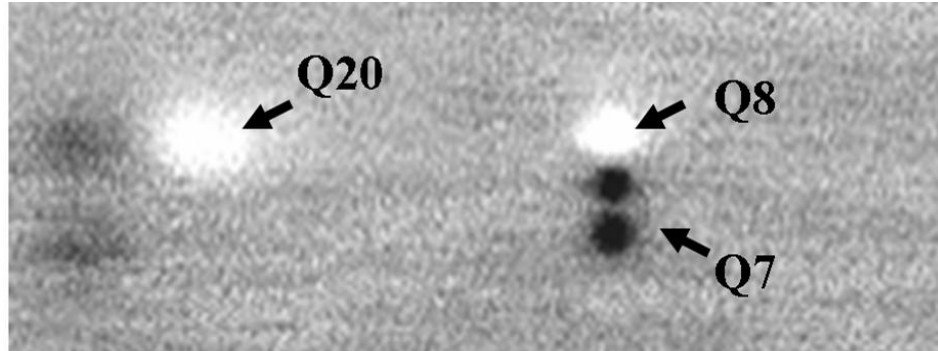
- Related to function
- Side channel

Understanding xVM images

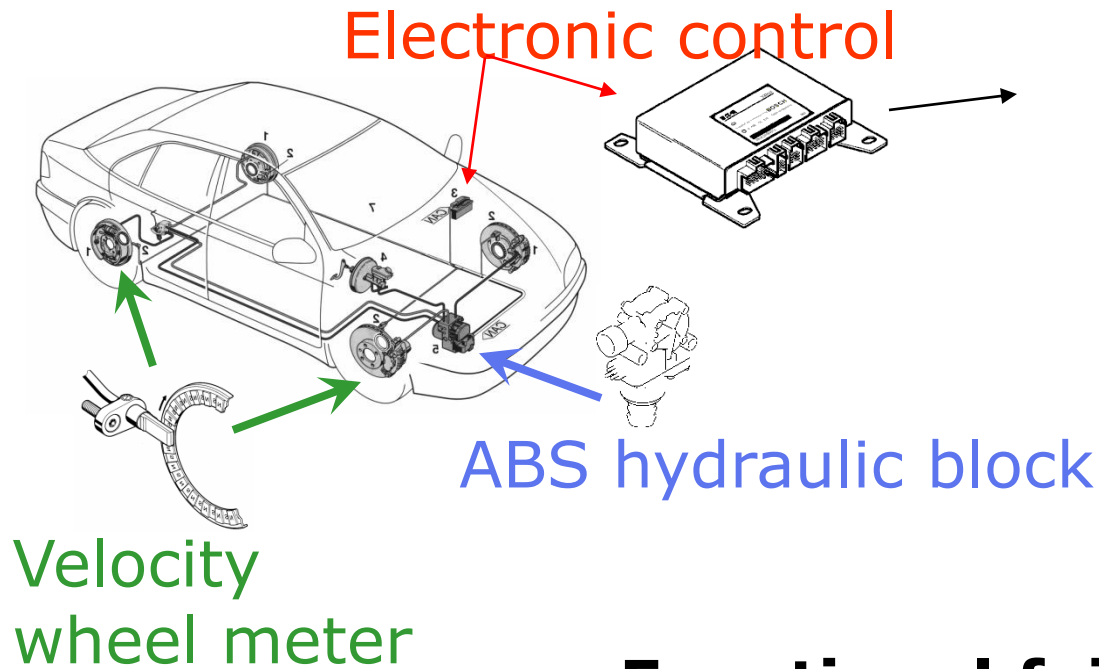
- Complex results
 - Even for good devices
 - All the sensitive areas are mapped
 - What is abnormal?
- Simulation approach
 - Understand the effect of laser stimulation on elementary structure
 - Understand how a defect modify it
 - Use these results at cell and full device level
- Can be reversely used (from signature to defect)



Simulation approach



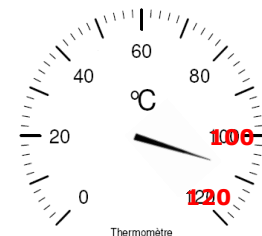
Soft defect failure analysis on MIXED mode Technology (1)



- **P**ower **C**ontrol **U**nit
Anti Lock **B**rake
System
- TQFP100
- 4 metal layers
- Mixed mode IC

Functional failure conditions

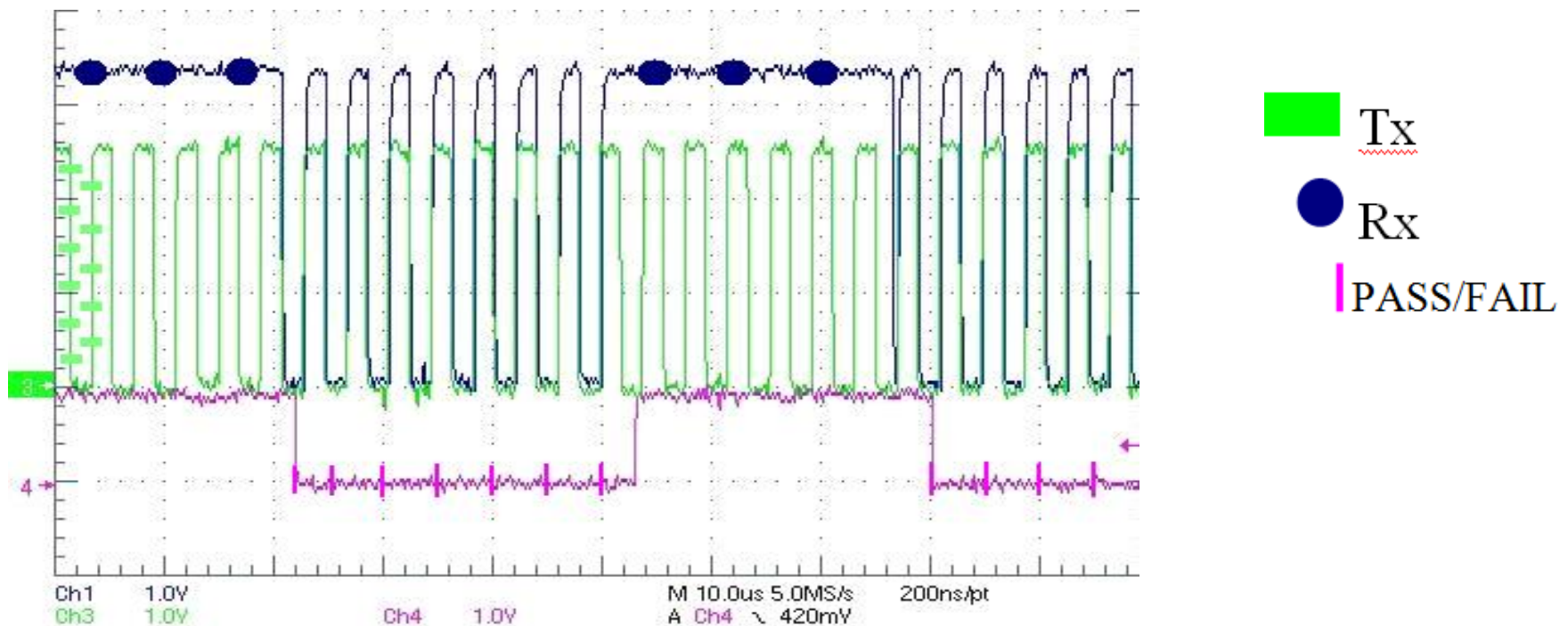
The device fails when temperature is over 100°C



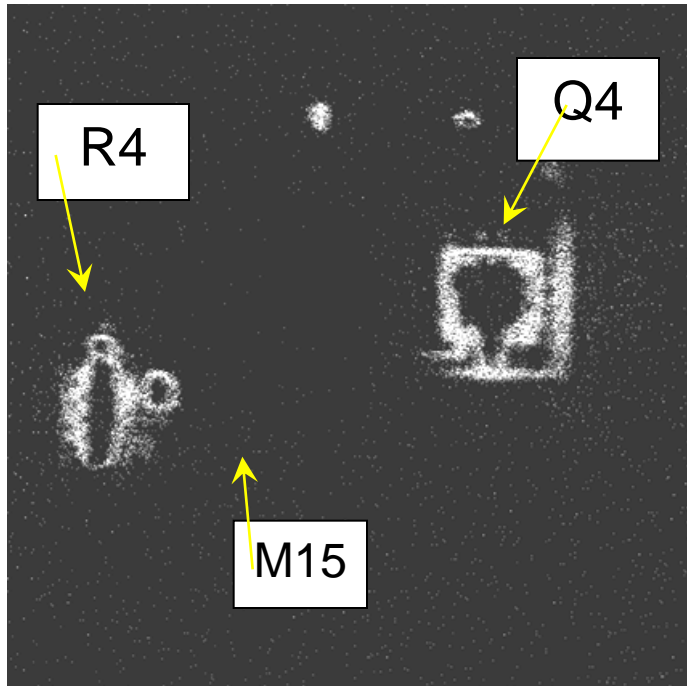
Soft defect failure analysis on MIXED mode Technology (2)

At high temperature, device becomes and stays fail

Electrical failure = No **Rx** signal = No data communication

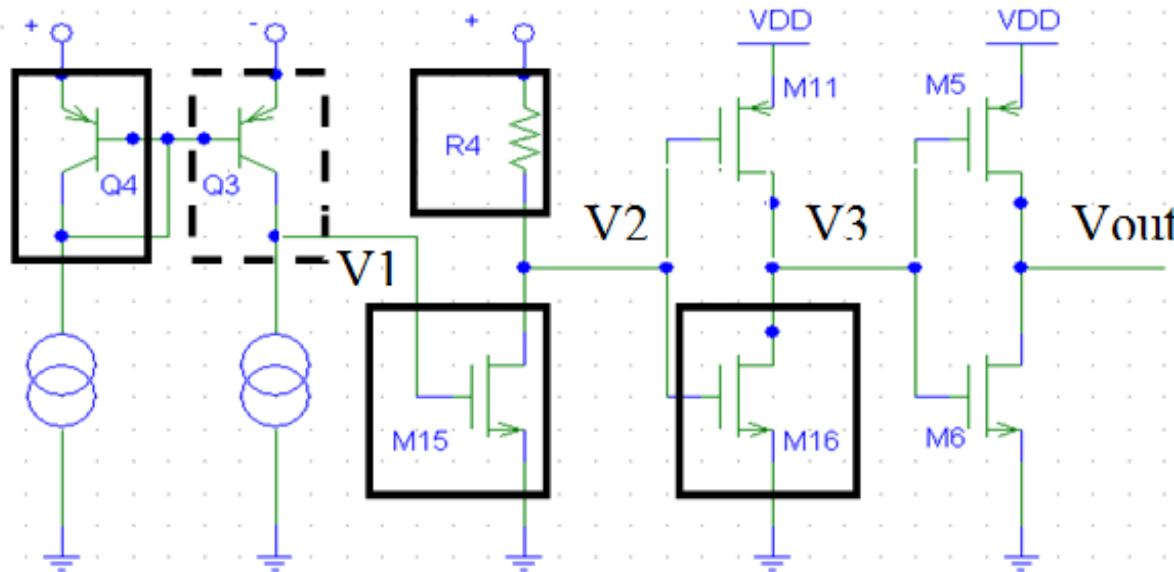


Soft defect failure analysis on MIXED mode Technology (3)

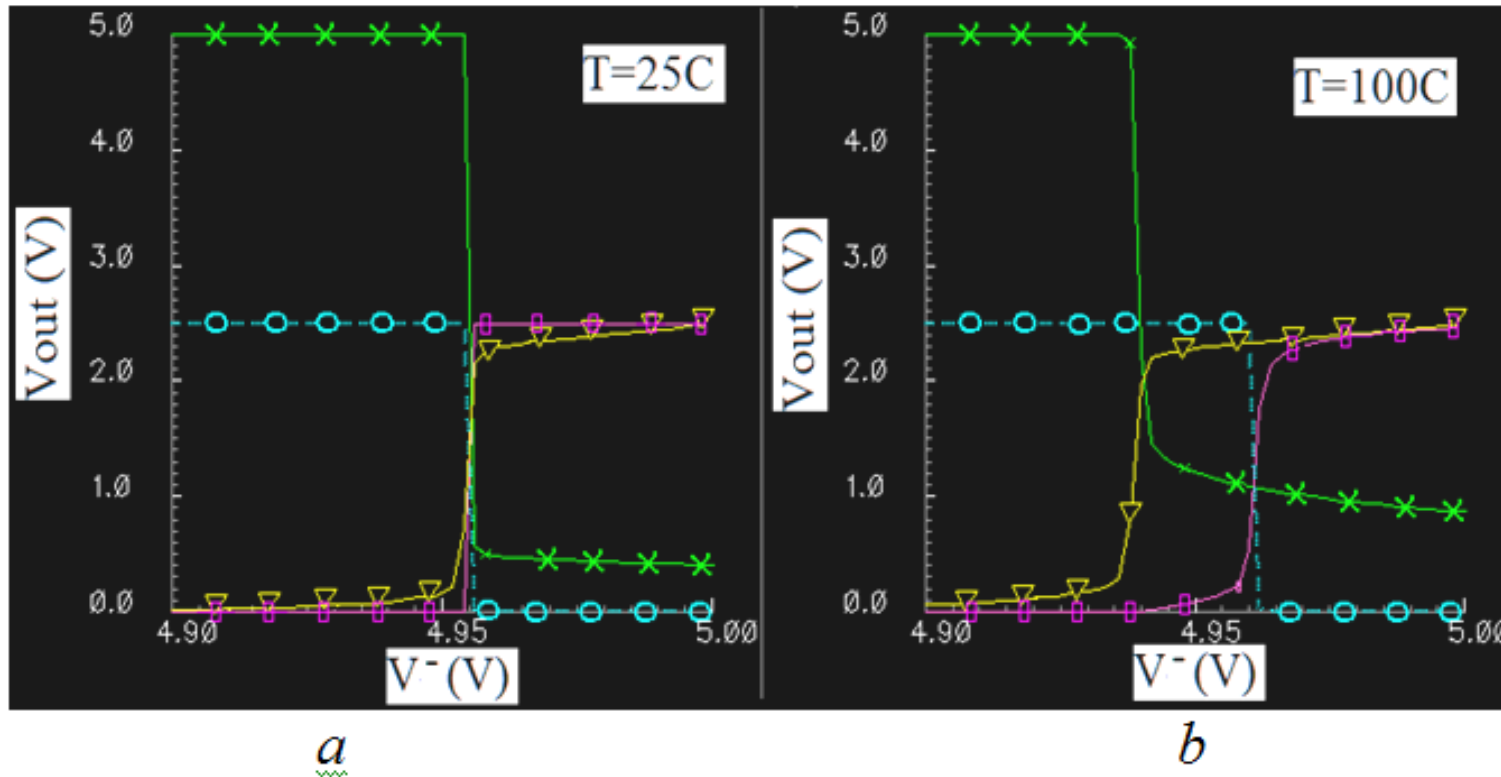


Simplified electrical schematic of sub block highlighted by DTLS techniques and simulated in Cadence

Backside DVM results: sensitive area under Thermal Laser Stimulation (TLS) for the temperature below 90°C (zoom: 80X).



Soft defect failure analysis on MIXED mode Technology (4)







R_{ds} of M15 is depends on T.

Undersized M15 (NMOS) transistor.

Example of design failure.

Electrical simulations: Plot of signal propagation in sub block highlighted by SDL at 25°C (a) and 100°C (b).

$V1$: , $V2$: , $V3$: , V_{out} : .

Multi xVM principle

■ FA Purpose

- One effect (delay, threshold ...) can be the result of different causes
- One defect can cause a lot of effects
- Looking simultaneously at a lot of effect helps to find the unique cause

■ Characterization purpose (need of multi channel)

■ Margin analysis

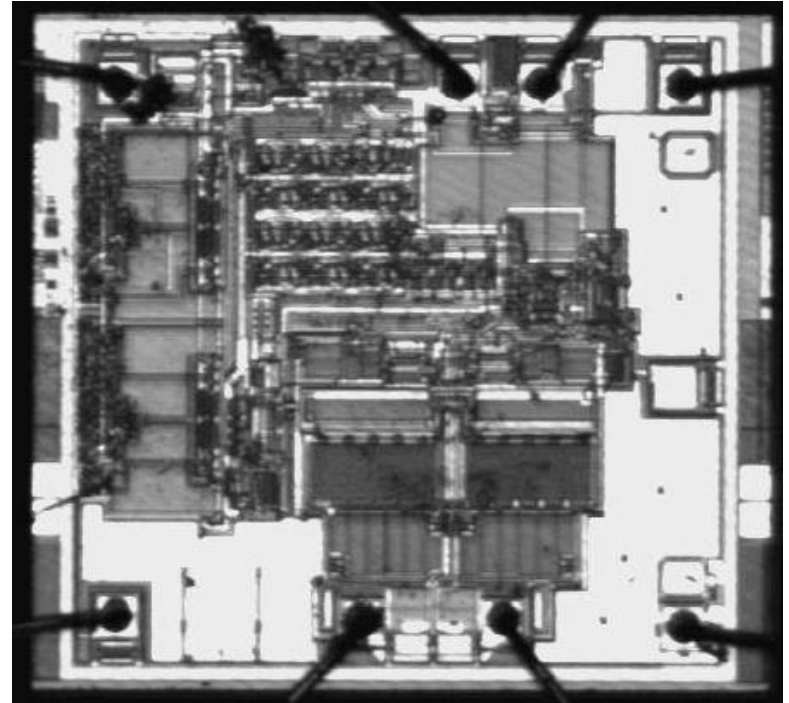
■ ...

■ Implementation

- Real time map often limited to 1 channel
- Multi channel acquisition performed at tester level
- For all samples (multi channel, one pixel) x,y position recorded
- Post processing of the data (could be quite real time with very slow scanning)

Multi xVM example

- Commercial, good device
- Operational amplifier set in a high gain configuration
- Bias condition: $V_+ = 1.5V$, $V_- = -1.5V$
- $V_{IN} = 50mV_{p-p}$ sinusoidal signal at 1kHz



- Channel 1: $I(t)$ + signal analysis
- Channel 2: $V(t)$ + signal analysis

